

Device Modeling Report

COMPONENTS: Light-Emitting Diode (LED) Professional
PART NUMBER: OSWT5161A
MANUFACTURER: OPTO SUPPLY
REMARK: TA=0 degree C

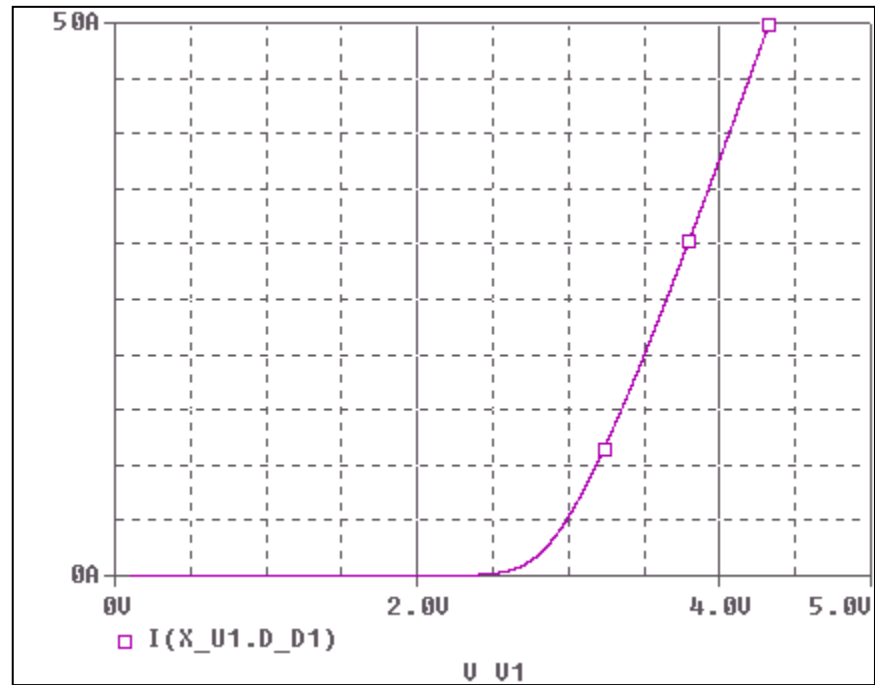


Bee Technologies Inc.

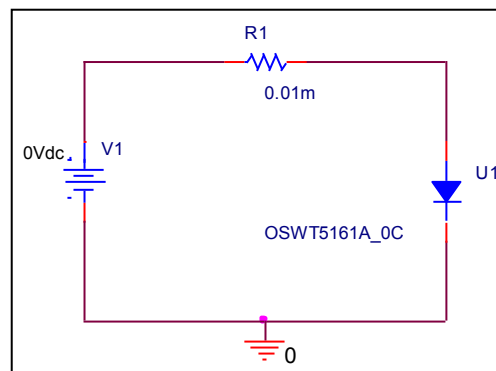
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

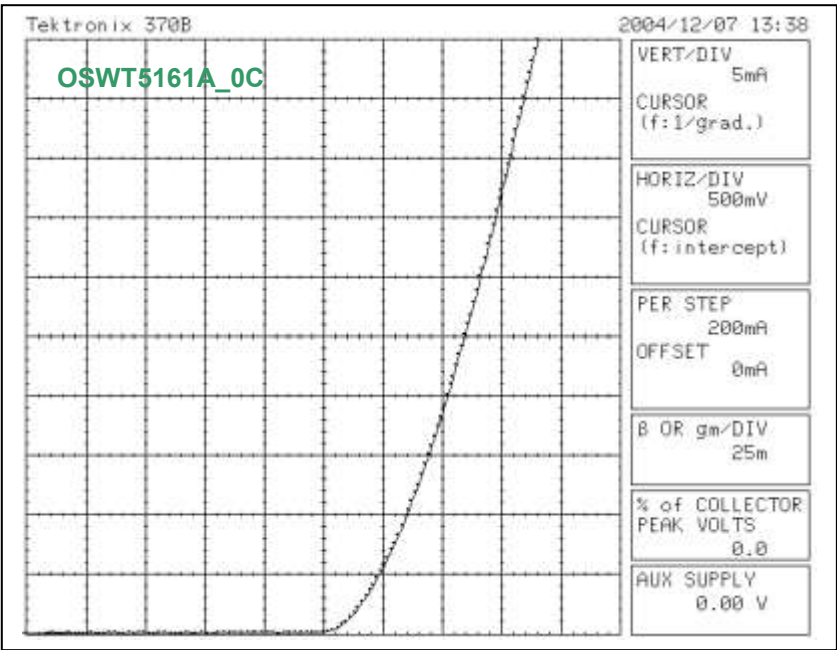


Evaluation Circuit



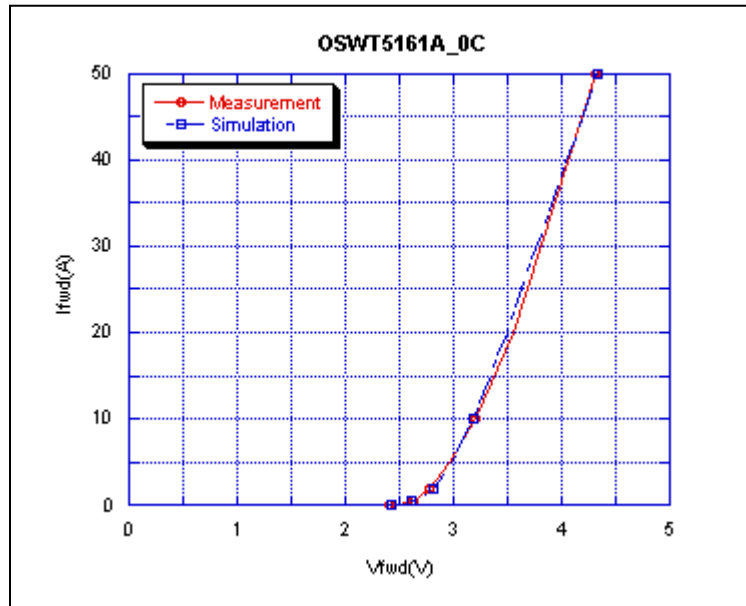
Forward Current Characteristic

Reference



Comparison Graph

Circuit Simulation Result

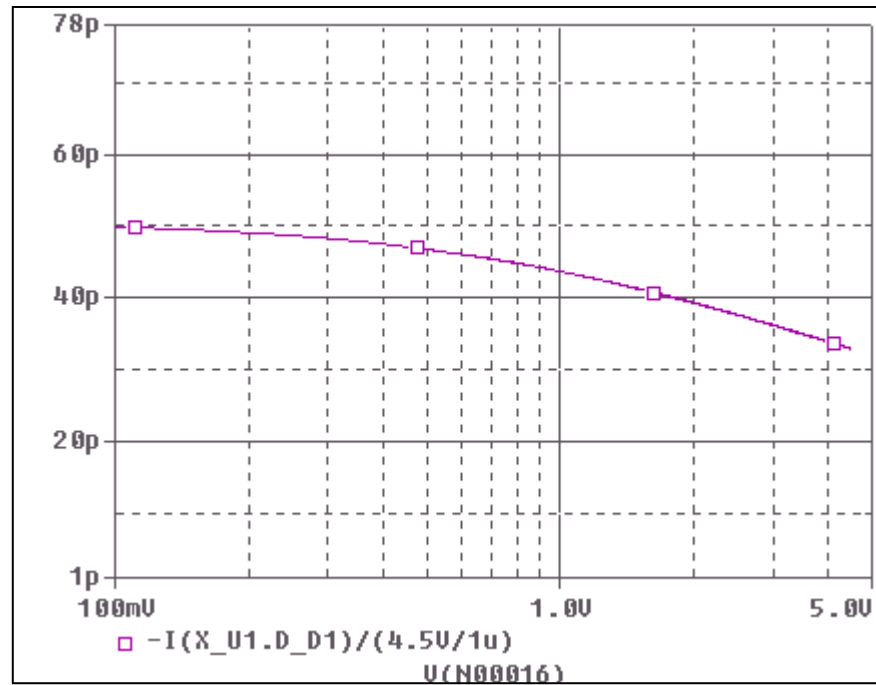


Simulation Result

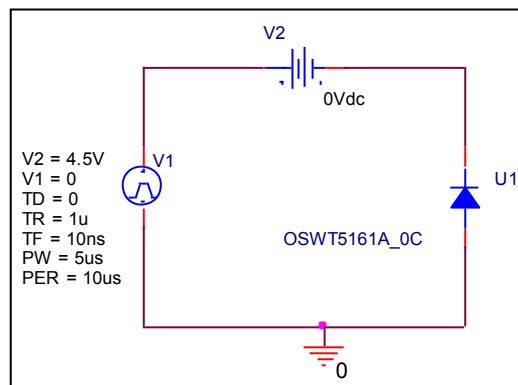
I_{fwd} (A)	V_{fwd} (V) Measurement	V_{fwd} (V) Simulation	%Error
0.1	2.41	2.427	0.705
0.2	2.545	2.505	1.5717
0.5	2.63	2.616	0.5323
1	2.69	2.706	0.5947
2	2.77	2.808	1.3718
5	2.955	2.984	0.9813
10	3.2	3.183	0.5312
20	3.55	3.503	1.3239
50	4.31	4.327	0.3944

Capacitance Characteristic

Circuit Simulation Result

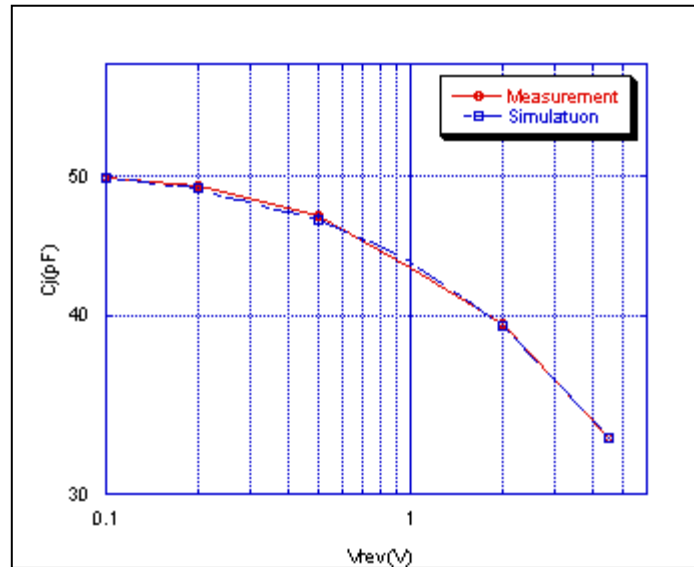


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

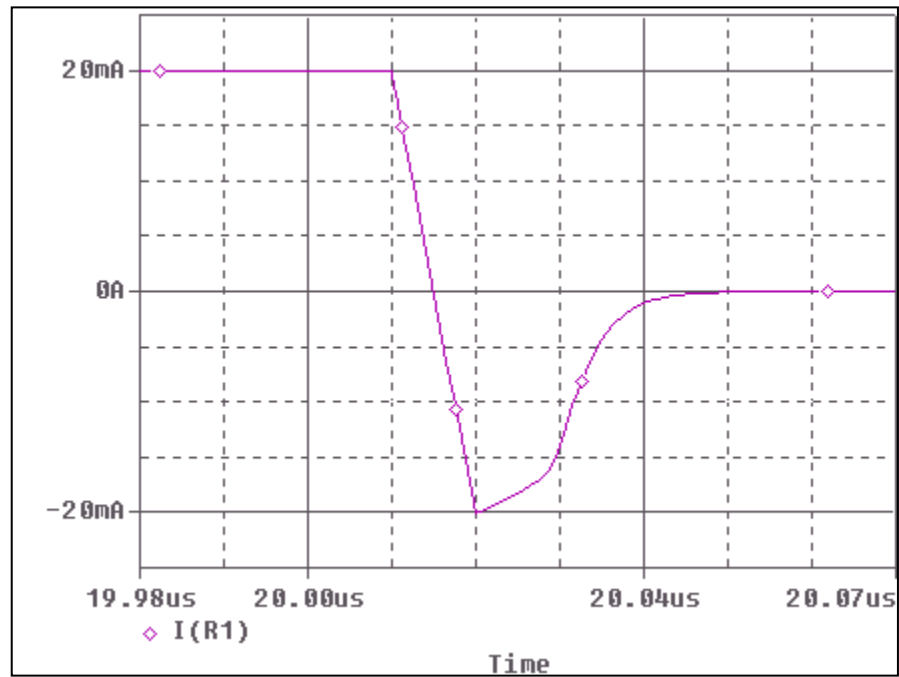


Simulation Result

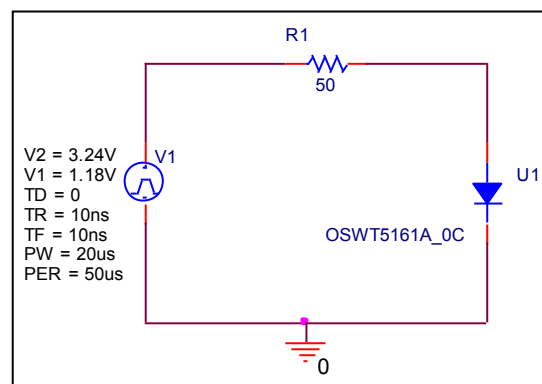
$V_{rev}(V)$	$C_j(pF)$ Measurement	$C_j(pF)$ Simulation	%Error
0	50.63	50.63	0
0.1	49.95	49.92	0.0600
0.2	49.25	49.07	0.3654
0.5	47.01	46.71	0.6381
1	43.15	43.65	1.1587
2	39.5	39.3	0.5063
4.5	32.86	32.9	0.1217

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

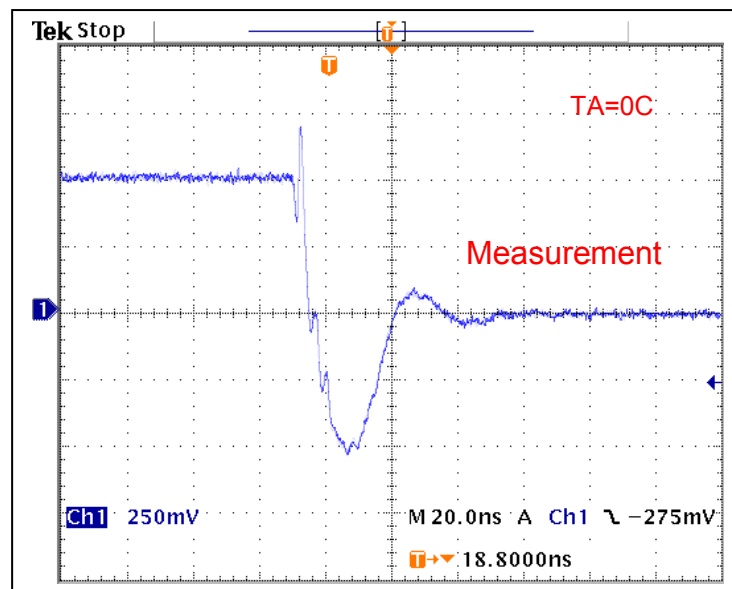


Compare Measurement vs. Simulation

Symbol	Measurement	Unit	Simulation	Unit	%Error
trj	9.2	ns	9.22	ns	0.2173
trb	13.2	ns	13.27	ns	0.5303

Reverse Recovery Characteristic

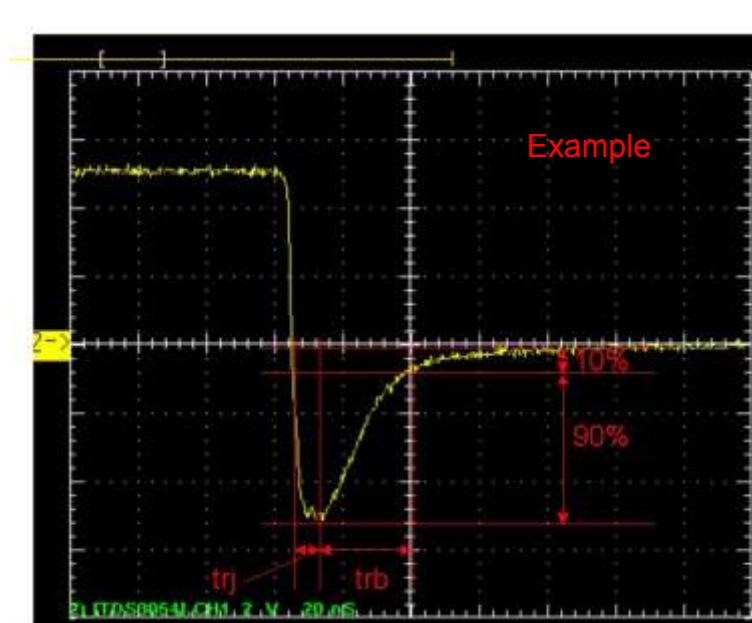
Reference



$\text{Trj} = 9.2(\text{ns})$

$\text{Trb} = 13.2(\text{ns})$

Conditions: $I_{\text{fwd}} = I_{\text{rev}} = 0.02(\text{A})$, $R_I = 50$



Relation between trj and trb